NSN 5961-01-194-8580

Transistor - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-194-8580

Inclosure Material:

Metal

Overall Length:

0.260 inches

Terminal Length:

0.500 inches

Overall Diameter:

0.370 inches

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-39

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Terminal

Terminal Circle Diameter:

0.200 inches

Features Provided:

Burn in and hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

80.0 breakdown voltage, collector-to-base, emitter open and 6.0 emitter to base voltage, static, collector open and 60.0 breakdown

voltage, collector-to-emitter, base open

Current Rating Per Characteristic:

5.00 amperes source cutoff current and 1.00 amperes source cutoff current

Power Rating Per Characteristic:

6.0 watts small-signal input power, common-collector absolute

Transfer Ratio:

240.0 static forward current transfer ratio, common-emitter

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Test Data Document:

18876-13229793 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,

etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

3 uninsulated wire lead

Shelf Life:

N/a

Unit Of Measure:

NSN 5961-01-194-8580

Transistor - Page 2 of 2

Demilitarization:

No

Fiig:

A110a0

